

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
-60V	10Ω @ V <sub>GS</sub> = -5V	-180mA

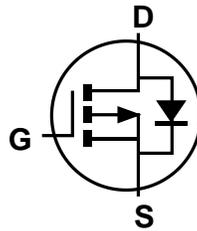
## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

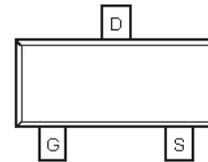
- General purpose interfacing switches
- Power management functions
- Analog switches



Top View



Equivalent Circuit



Top View

## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([DMP610DLQ](#))**

## Mechanical Data

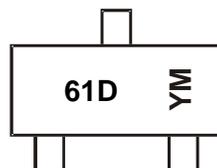
- Package: SOT23
- Package Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP610DL-7	SOT23	3,000	Tape & Reel
DMP610DL-13	SOT23	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



61D = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: K = 2023)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2016	...	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	D	...	K	L	M	N	O	P	R	S	T	U

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-60	V
Gate-Source Voltage			V <sub>GSS</sub>	±30	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-180	mA
		T <sub>A</sub> = +70°C		-130	
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-0.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-1.2	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	405	°C/W
Total Power Dissipation (Note 6)			P <sub>D</sub>	500	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	251	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.8	—	-2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	10	Ω	V <sub>GS</sub> = -5V, I <sub>D</sub> = -0.1A
Forward Transconductance	g <sub>FS</sub>	—	0.25	—	S	V <sub>DS</sub> = -25V, I <sub>D</sub> = -0.1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>ISS</sub>	—	24.6	—	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	4.8	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	2.8	—	pF	
Gate Resistance	R <sub>G</sub>	—	242	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>G</sub>	—	280	—	pC	V <sub>DS</sub> = -10V, I <sub>D</sub> = -100mA
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>G</sub>	—	560	—	pC	
Gate-Source Charge	Q <sub>GS</sub>	—	90	—	pC	
Gate-Drain Charge	Q <sub>GD</sub>	—	77	—	pC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.8	—	ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A, R <sub>GEN</sub> = 50Ω, V <sub>GS</sub> = -10V
Turn-On Rise Time	t <sub>R</sub>	—	2.6	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	11.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	7.2	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

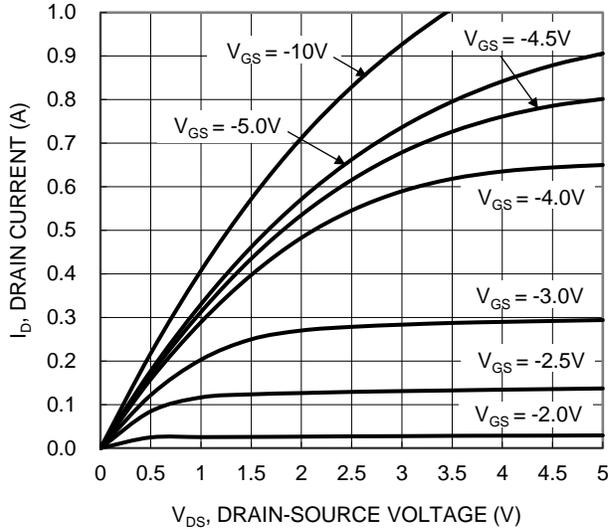


Figure 1. Typical Output Characteristic

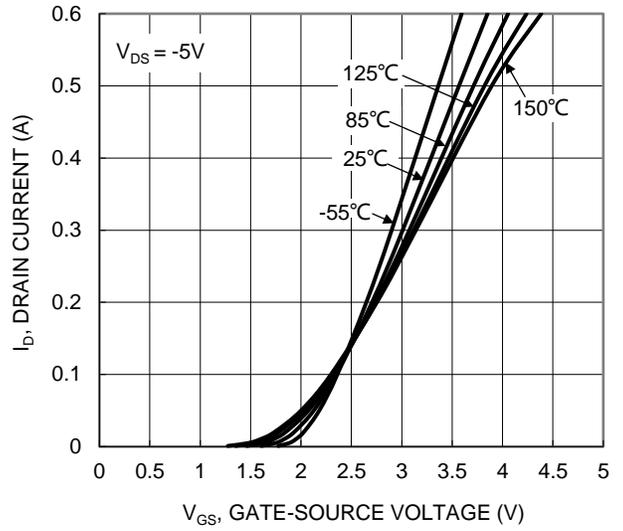


Figure 2. Typical Transfer Characteristic

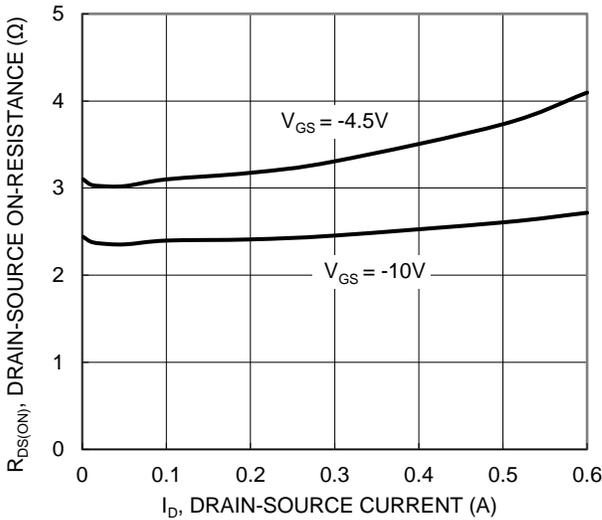


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

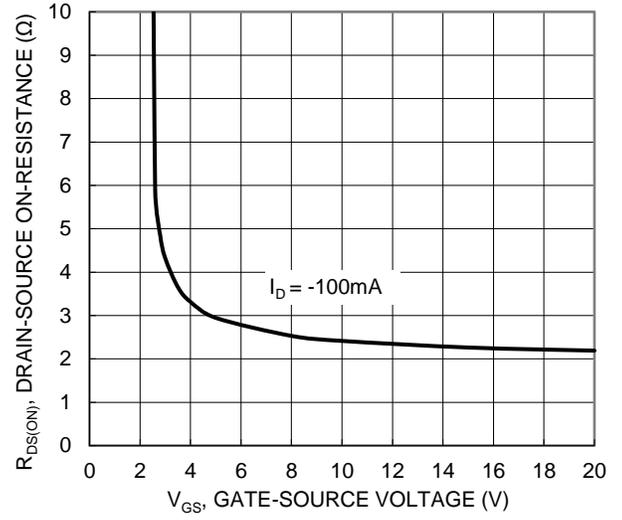


Figure 4. Typical Transfer Characteristic

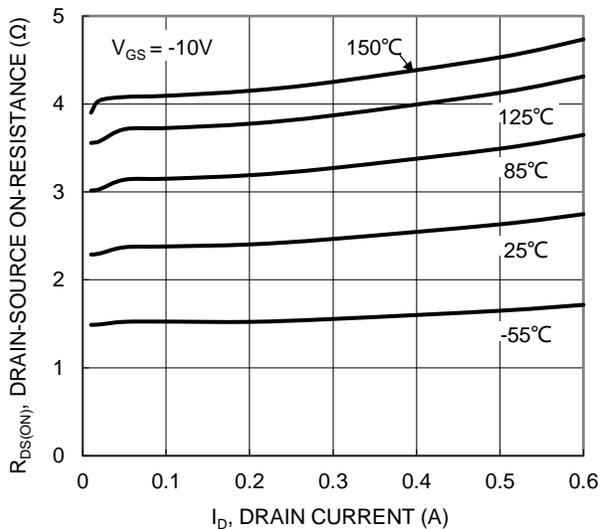


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

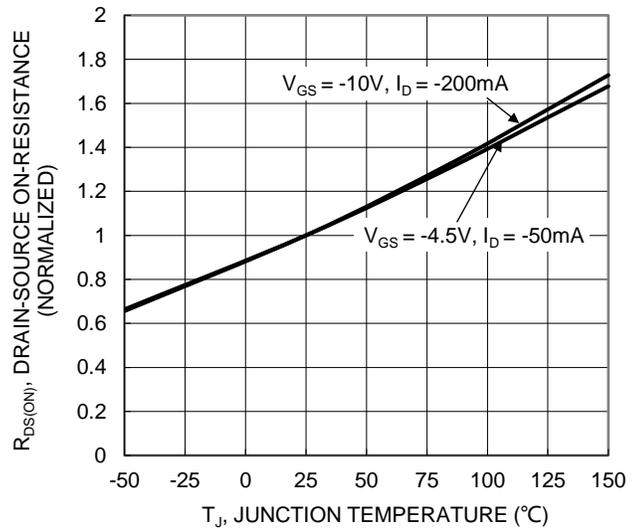


Figure 6. On-Resistance Variation with Temperature

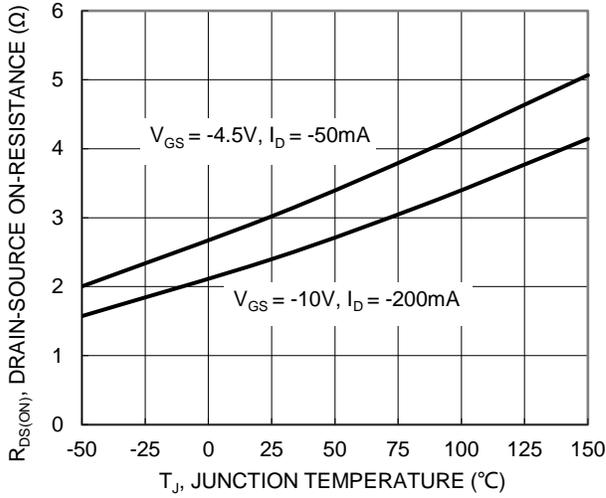


Figure 7. On-Resistance Variation with Temperature

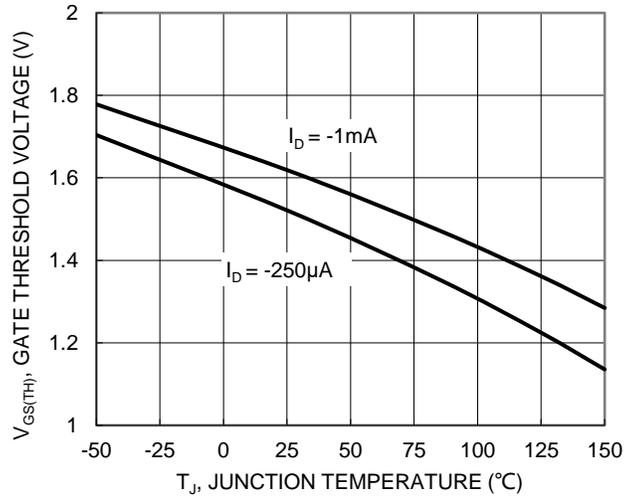


Figure 8. Gate Threshold Variation vs. Junction Temperature

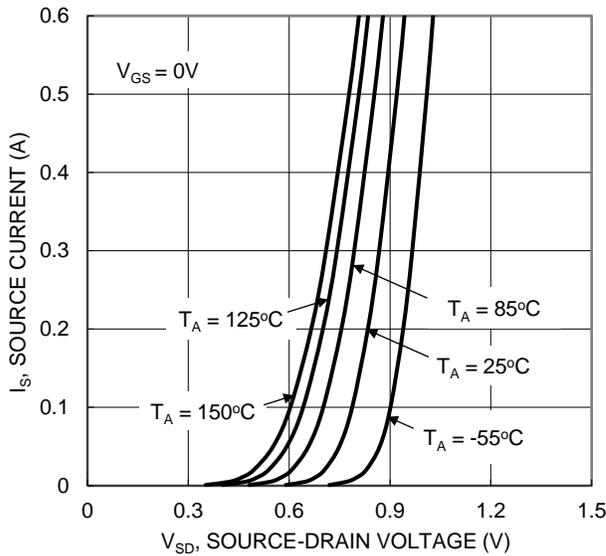


Figure 9. Diode Forward Voltage vs. Current

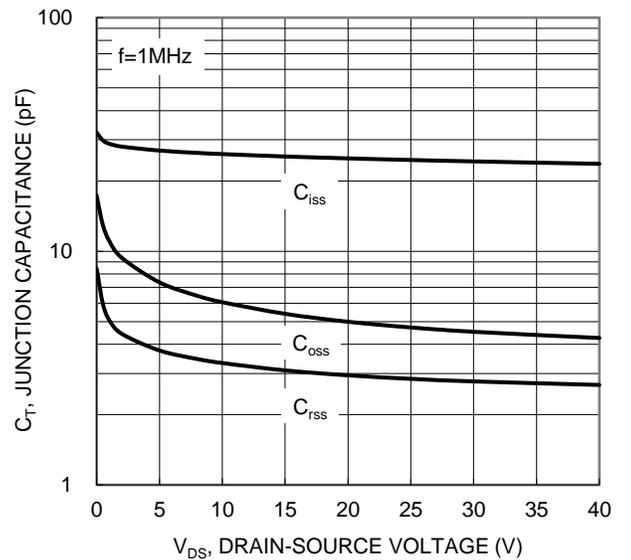


Figure 10. Typical Junction Capacitance

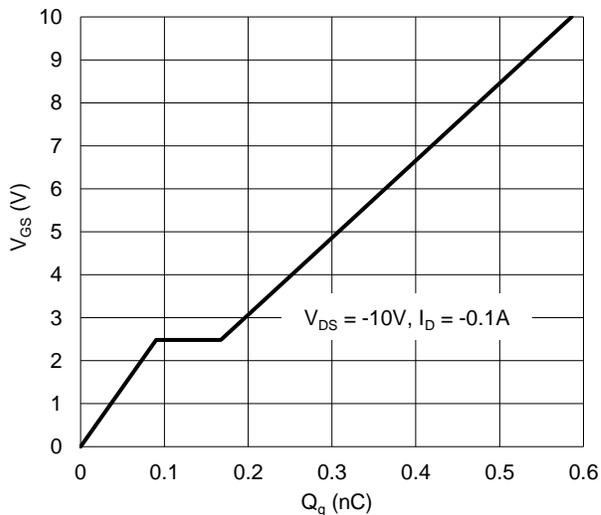


Figure 11. Gate Charge

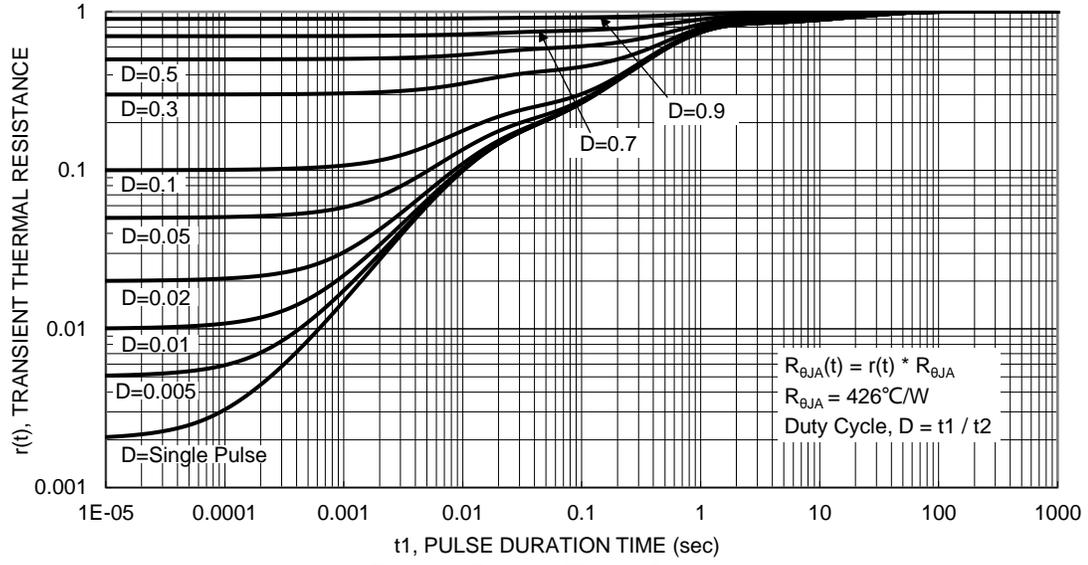
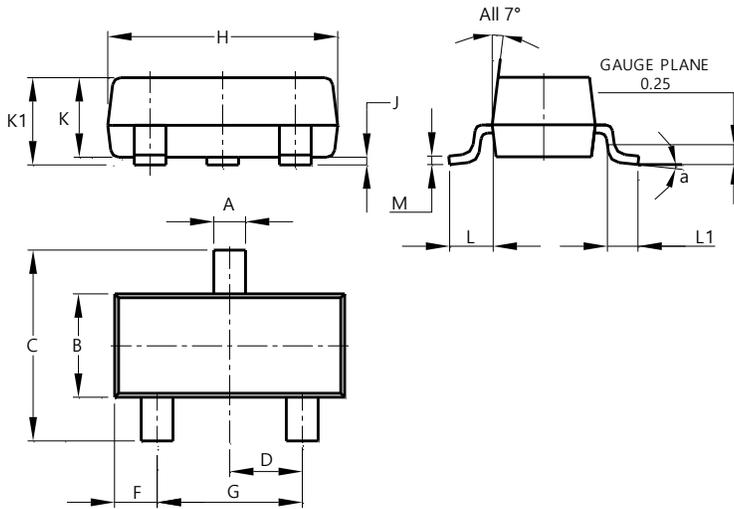


Figure 12. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

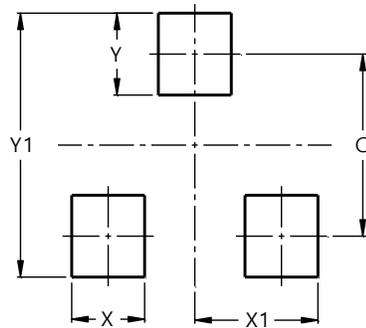


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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